

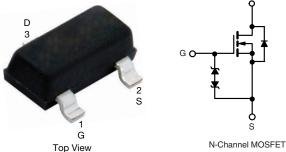
Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.085			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.130			
I _D (A)	4			
Configuration	Single			

SOT-23 (TO-236)

Marking Code: 8Mxxx



FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^c
- 100 % R_q and UIS Tested
- Typical ESD Protection 800 V
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2360EES-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	s otherwise noted)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	T _C = 25 °C	- I _D -	4	
Continuous Drain Current	T _C = 125 °C		2.3	
Continuous Source Current (Diode Conduction)		IS	3.7	A
Pulsed Drain Current ^a		I _{DM}	16	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	6	
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	1.8	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	D	3	W
	T _C = 125 °C	P _D	1	vv
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R _{thJA}	166	°C/W
Junction-to-Foot (Drain)		R _{thJF}	50	0/₩

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μΑ	1.5	-	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 5.5	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 6 A, T _J = 25 °C	-	0.058	0.085	
		V _{GS} = 10 V	I _D = 6 A, T _J = 125 °C	-	-	0.197	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 6 A, T _J = 175 °C	-	-	0.258	
		V _{GS} = 4.5 V	I _D = 5 A	-	0.081	0.130	Ω
Forward Transconductance b	9 _{fs}	V _{DS} = -15 V, I _D = 1.9 A		-	5.8	-	S
Dynamic ^b					•		
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	295	370	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	55	70	
Reverse Transfer Capacitance	C _{rss}			-	35	55	
Total Gate Charge ^c	Qg			-	7.40	12	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 2 \text{ A}$	-	0.95	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	1.94	-	
Gate Resistance	R _g	f = 1 MHz		1.24	2.46	3.68	Ω
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 30 \text{ V}, \text{ R}_{\text{L}} = 15 \ \Omega$ $\text{I}_{\text{D}} \cong 2 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \ \Omega$		-	5	8	
Rise Time ^c	t _r			-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	10	15	
Fall Time ^c	t _f	1	1		8	12	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	16	Α
Forward Voltage	V _{SD}	$I_{\rm F} = 1.5 \text{A}, V_{\rm GS} = 0$		-	0.8	1.2	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

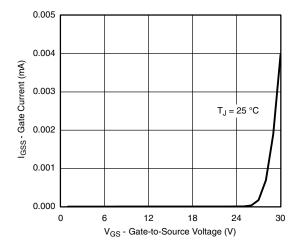
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

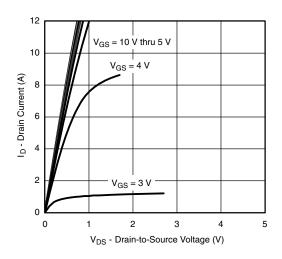


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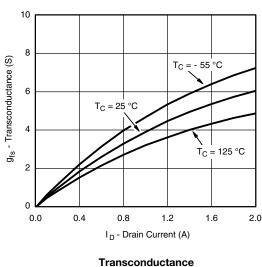
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Gate Current vs. Gate-Source Voltage

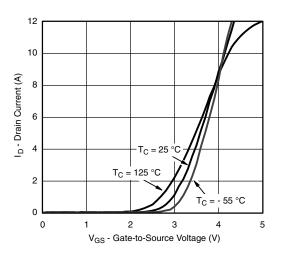




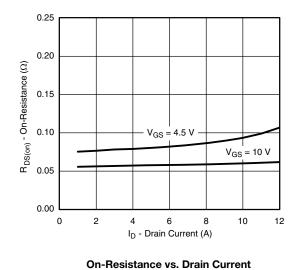


 10^{-2} 10^{-4} 10^{-4} 10^{-6} 10^{-6} 10^{-6} 10^{-6} 10^{-10} 0 10^{-10} 0 10^{-10} 0 10^{-10} 0 12 18 24 30 V_{GS} - Gate-to-Source Voltage (V)

Gate Current vs. Gate-Source Voltage



Transfer Characteristics



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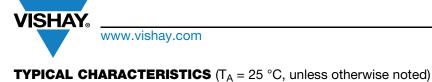
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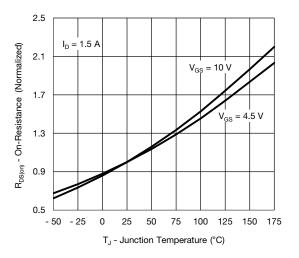


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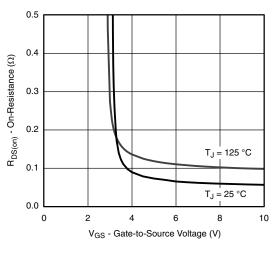


600 500 C - Capacitance (pF) 400 $\mathbf{C}_{\mathrm{iss}}$ 300 200 100 C_{rss} 0 10 20 30 40 50 60 0 V_{DS} - Drain-to-Source Voltage (V)

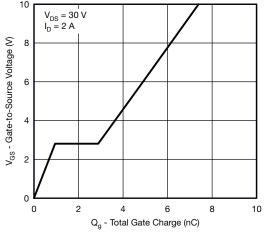
Capacitance



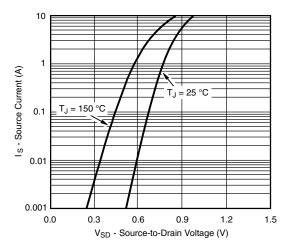
On-Resistance vs. Junction Temperature



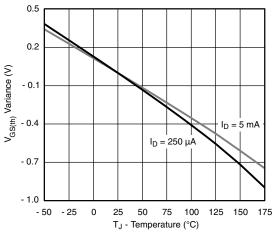
On-Resistance vs. Gate-Source Voltage



Gate Charge







Threshold Voltage

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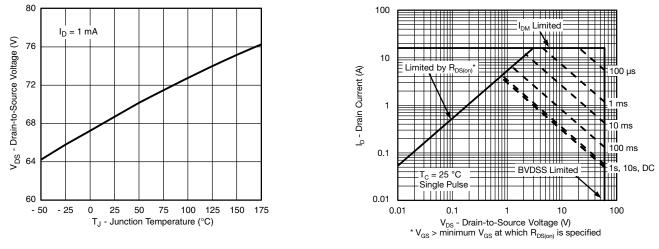
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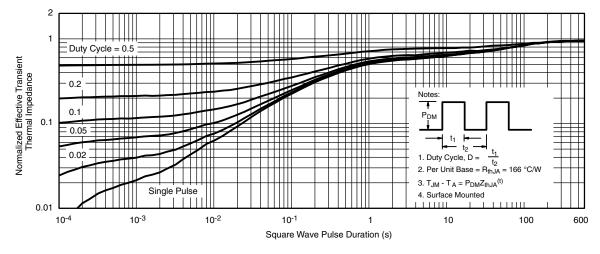
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Drain-Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



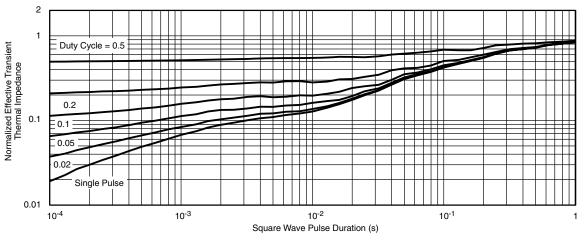
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65352.



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REVISION	REVISION HISTORY ^a				
REVISION	DATE	DESCRIPTION OF CHANGE			
F	04-Apr-14	 Correction of R_{DS(on)} value used in calculation of maximum continuous drain current and safe operating area curve. V_{GS} = 4.5 V curve added to on-resistance vs. junction temperature graph. 			

Note

a. As of April 2014



Package Information

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SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES			
Dim	Min	Max	Min	Мах		
Α	0.89	1.12	0.035	0.044		
A ₁	0.01	0.10	0.0004	0.004		
A ₂	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E ₁	1.20	1.40	0.047	0.055		
е	0.95	0.95 BSC		0.0374 Ref		
e ₁	1.90	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024		
L ₁	0.64 Ref		0.025 Ref			
S	0.50 Ref		0.020 Ref			
q	3°	8°	3°	8°		



Application Note 826

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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Revision: 01-Jan-2025